TOSHIBA 1DL42A

TOSHIBA HIGH EFFICIENCY RECTIFIER (HED) SILICON EPITAXIAL JUNCTION TYPE

DL42A

SWITCHING TYPE POWER SUPPLY APPLICATIONS

Repetitive Peak Reverse Voltage $: V_{RRM} = 200 V$

Average Forward Current $: I_{F(AV)} = 1.0 A$

Very Fast Reverse-Recovery Time : $t_{rr} = 35 \text{ ns}$ (Max.)

 $: V_{FM} = 0.98 V \text{ (Max.)}$ Low Forward Voltage

Available to Reduce Switching Losses and Output Noise.

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Reverse Voltage	v_{RRM}	200	V	
Average Forward Current	I _F (AV)	1.0	A	
Peak One Cycle Surge Forward	Incre	30 (50 Hz)	A	
Current (Non-Repetitive)	I_{FSM}	33 (60 Hz)		
Junction Temperature	T_{j}	-40~150	$^{\circ}\mathrm{C}$	
Storage Temperature Range	$\mathrm{T_{stg}}$	-40~150	°C	

Ø 0.6 1. ANODE 2. CATHODE **JEDEC EIAJ TOSHIBA** 3-3F2A

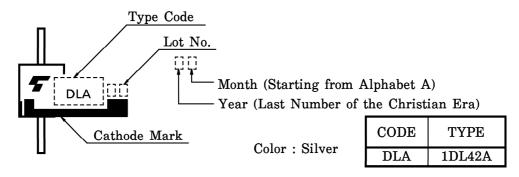
Unit in mm

Weight: 0.18 g

ELECTRICAL CHARACTERISTICS ($Ta = 25^{\circ}C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	v_{FM}	$I_{\text{FM}} = 1.0 \text{ A}$	_	_	0.98	V
Repetitive Peak Reverse Current	$I_{ m RRM}$	$V_{RRM} = 200 V$	_	_	100	μ A
Reverse Recovery Time	t_{rr}	$I_{\rm F} = 1 {\rm A, di / dt} = -30 {\rm A / \mu s}$	_	_	35	ns
Forward Recovery Time	t_{fr}	$I_{ m F}=1.0~{ m A}$	_	_	100	ns

MARKING



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